NX7002AKA

60 V, single N-channel Trench MOSFET

18 February 2013

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Very fast switching
- Trench MOSFET technology
- ESD protected
- AEC-Q101 qualified

3. Applications

- · Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	-	60	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{sp} = 25 °C		-	-	300	mA
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	190	mA
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 100 \text{ mA}; T_j = 25 \text{ °C}$		-	3	4.5	Ω

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².





60 V, single N-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u></u> 3	D I
2	S	source		
3	D	drain	1	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
NX7002AKA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _{amb} = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{sp} = 25 °C		-	300	mA
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	190	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	120	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	760	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C	[<u>2]</u>	-	265	mW
			[1]	-	325	mW
		T _{sp} = 25 °C		_	1330	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	diode					,
I _S	source current	T _{amb} = 25 °C	[1]	-	190	mA

60 V, single N-channel Trench MOSFET

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

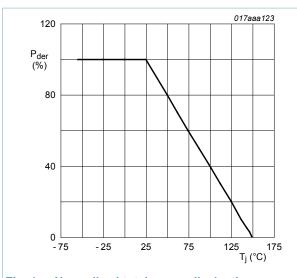


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

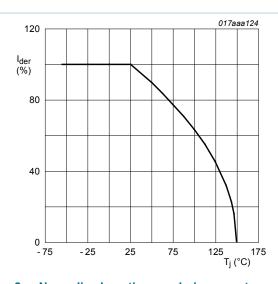
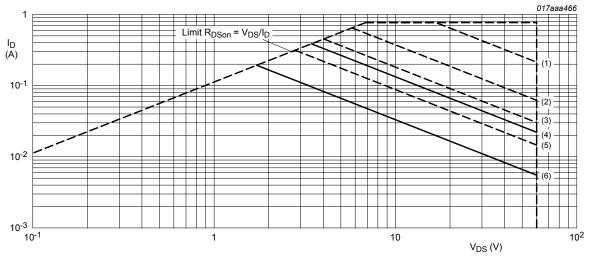


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$



I_{DM} = single pulse

(1) $t_p = 100 \mu s$

(2) $t_p = 1 \text{ ms}$

(3) $t_p = 10 \text{ ms}$

(4) DC; T_{sp} = 25 °C

 $(5) t_p = 100 \text{ ms}$

(6) DC; $T_{amb} = 25 \, ^{\circ}C$; drain mounting pad 1 cm²

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

NX7002AKA

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60 V, single N-channel Trench MOSFET

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Thermal characteristics

Table 5. Thermal characteristics

NX7002AKA

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	-	[1]	-	410	470	K/W
			[2]	-	330	380	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	95	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

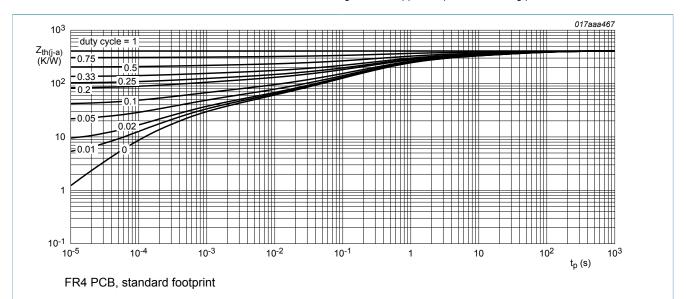


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

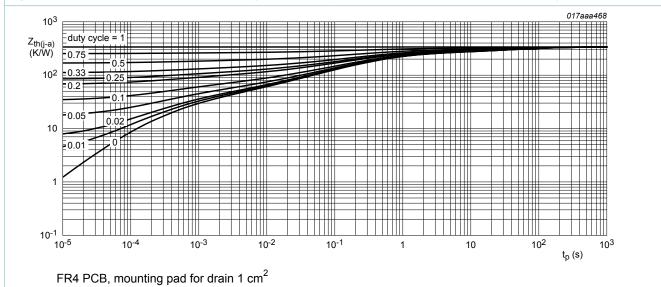


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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60 V, single N-channel Trench MOSFET

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.1	1.6	2.1	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μA
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.5	μA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.5	μA
		V _{GS} = 5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 100 mA; T _j = 25 °C	-	3	4.5	Ω
	resistance	V _{GS} = 10 V; I _D = 100 mA; T _j = 150 °C	-	6.2	9.2	Ω
		V _{GS} = 5 V; I _D = 100 mA; T _j = 25 °C	-	3.7	5.2	Ω
g _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 200 mA; T_{j} = 25 °C	-	230	-	mS
Dynamic c	haracteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = 30 \text{ V}; I_D = 200 \text{ mA}; V_{GS} = 4.5 \text{ V};$	-	0.33	0.43	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.12	-	nC
Q_{GD}	gate-drain charge		-	0.09	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	11	17	pF
C _{oss}	output capacitance	T _j = 25 °C	-	3.4	-	pF
C _{rss}	reverse transfer capacitance		-	1.4	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 40 V; R_L = 250 Ω ; V_{GS} = 10 V;	-	6	12	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	7	-	ns
$t_{d(off)}$	turn-off delay time		-	20	40	ns
t _f	fall time		-	14	-	ns
Source-dra	in diode		1			
V_{SD}	source-drain voltage	I _S = 115 mA; V _{GS} = 0 V; T _i = 25 °C	0.47	0.7	1.2	V

60 V, single N-channel Trench MOSFET

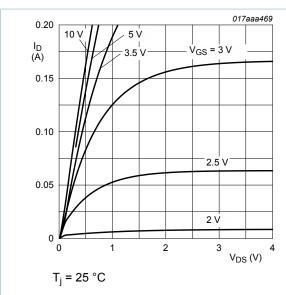
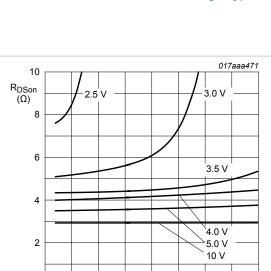


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



T_i = 25 °C

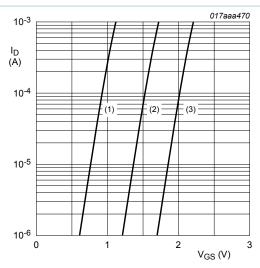
0.05

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

0.10

0.15

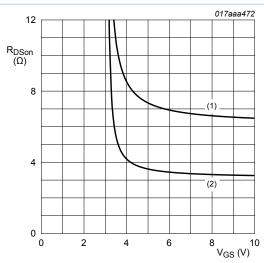
0.20



 T_i = 25 °C; V_{DS} = 5 V

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



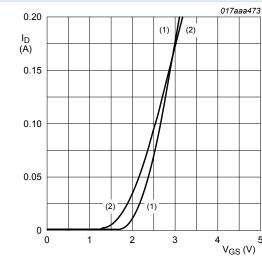
 $I_D = 0.2 A$

(1) $T_i = 150 \, ^{\circ}C$

(2) $T_i = 25 \, ^{\circ}C$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

60 V, single N-channel Trench MOSFET



 $V_{DS} > I_{D} \times R_{DSon}$

(1) $T_j = 25 \,^{\circ}\text{C}$ (2) $T_i = 150 \,^{\circ}\text{C}$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

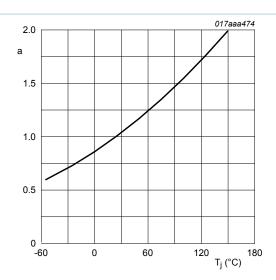
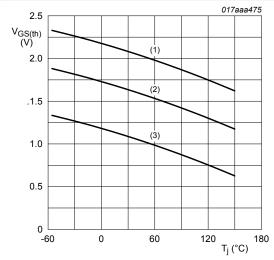


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

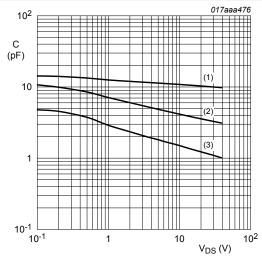
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 I_D = 0.25 mA; V_{DS} = V_{GS}

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

7/14

60 V, single N-channel Trench MOSFET

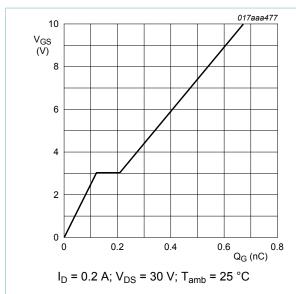


Fig. 14. Gate-source voltage as a function of gate charge; typical values

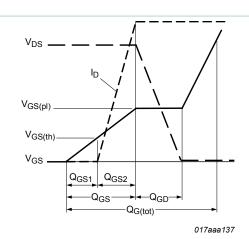
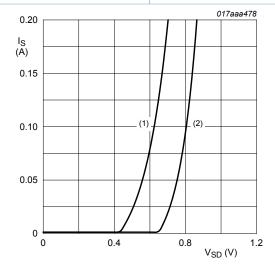


Fig. 15. Gate charge waveform definitions



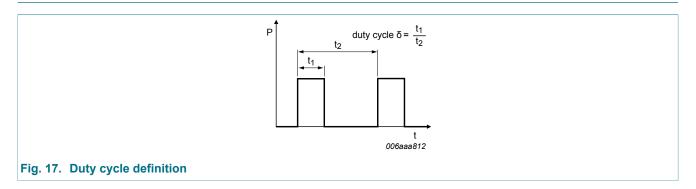
 $V_{GS} = 0 V$ (1) $T_j = 150 \,^{\circ}C$

(2) $T_i = 25 \, ^{\circ}C$

Fig. 16. Source current as a function of source-drain voltage; typical values

60 V, single N-channel Trench MOSFET

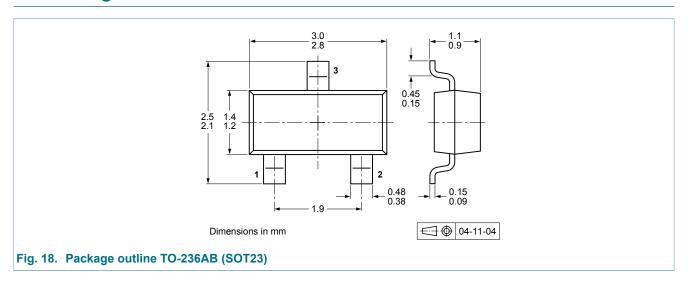
10. Test information



10.1 Quality information

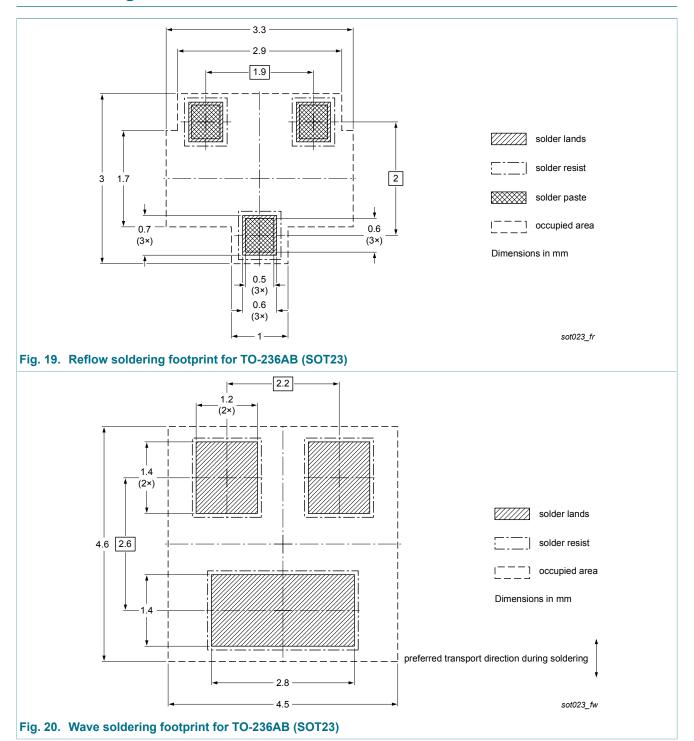
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

11. Package outline



60 V, single N-channel Trench MOSFET

12. Soldering



60 V, single N-channel Trench MOSFET

13. Revision history

Table 7. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NX7002AKA v.1	20130218	Product data sheet	-	-

60 V, single N-channel Trench MOSFET

14. Legal information

14.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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NX7002AKA

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60 V, single N-channel Trench MOSFET

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13 / 14

60 V, single N-channel Trench MOSFET

15. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Limiting values	2
8	Thermal characteristics	4
9	Characteristics	5
10	Test information	9
10.1	Quality information	
11	Package outline	9
12	Soldering	10
13	Revision history	11
14	Legal information	12
14.1	Data sheet status	12
14.2	Definitions	12
14.3	Disclaimers	12
14.4	Trademarks	13

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